



## Description

The DMP3018SFV-13 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = -30V$   $I_D = -55A$

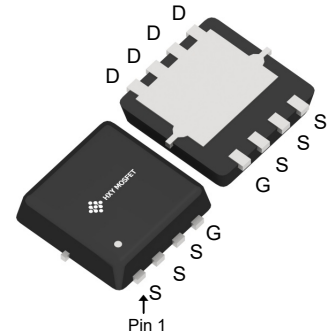
$R_{DS(ON)} < 11m\Omega$  @  $V_{GS} = -10V$

## Application

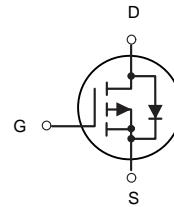
Battery protection

Load switch

Uninterruptible power supply



DFN3X3-8L



P-Channel MOSFET

## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMP3018SFV-13	DFN3X3-8L	HXY MOSFET	5000

## Absolute Maximum Ratings ( $T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	-55	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	-23	A
IDM	Pulsed Drain Current <sup>2</sup>	-140	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	78.8	mJ
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	21.5	W
TSTG	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	5.8	°C/W



**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

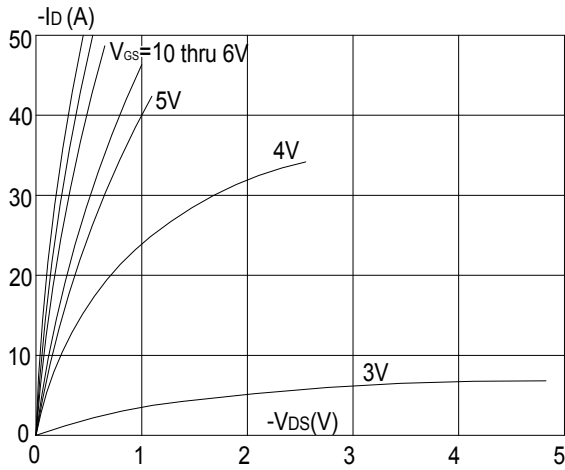
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D = -250\mu A$	-30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V,$	-	-	-1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS} = -10V, I_D = -12A$	-	8.5	11	m $\Omega$
		$V_{GS} = -4.5V, I_D = -8A$	-	13	18	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$	-	2800	-	pF
$C_{oss}$	Output Capacitance		-	346	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	319	-	pF
$Q_g$	Total Gate Charge	$V_{DS} = -15V, I_D = -20A,$ $V_{GS} = -10V$	-	30	-	nC
$Q_{gs}$	Gate-Source Charge		-	5.3	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	7.6	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -15V, I_D = -20A,$ $V_{GS} = -10V, R_{GEN} = 2.5\Omega$	-	14	-	ns
$t_r$	Turn-on Rise Time		-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	95	-	ns
$t_f$	Turn-off Fall Time		-	65	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	-55	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-140	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S = -35A$	-	-0.8	-1.2	V

- Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature  
 2. EAS condition:  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = -20V$ ,  $V_G = -10V$ ,  $L = 0.5mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = -17A$   
 3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$

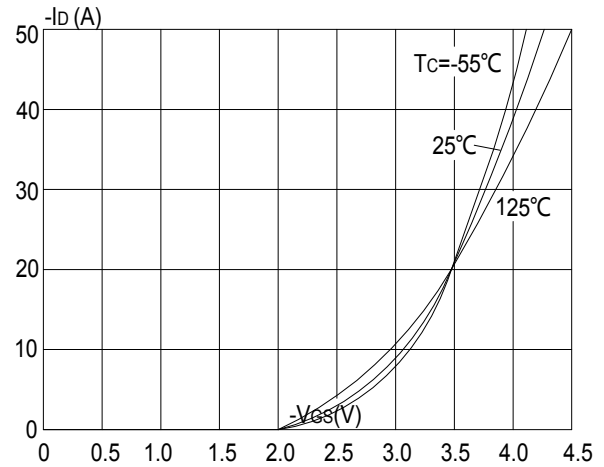


## Typical Performance Characteristics

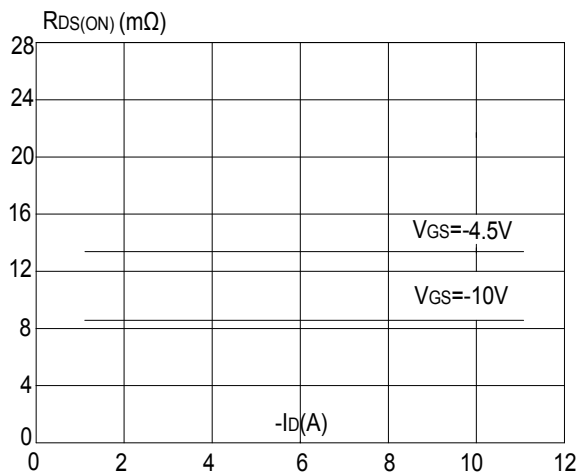
**Figure 1: Output Characteristics**



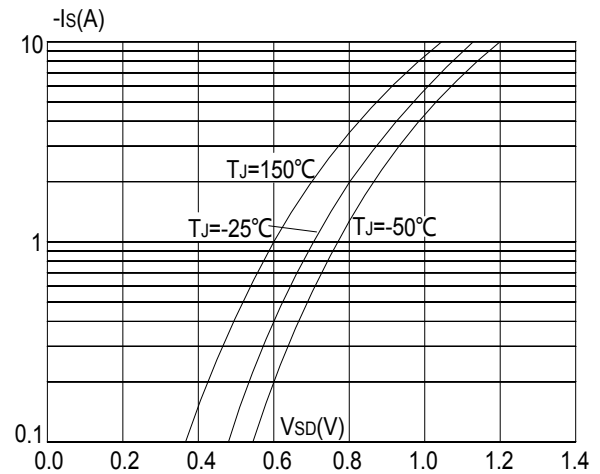
**Figure 2: Typical Transfer Characteristics**



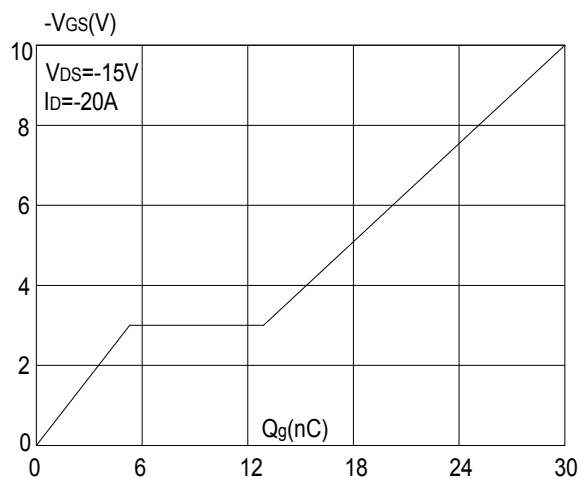
**Figure 3: On-resistance vs. Drain Current**



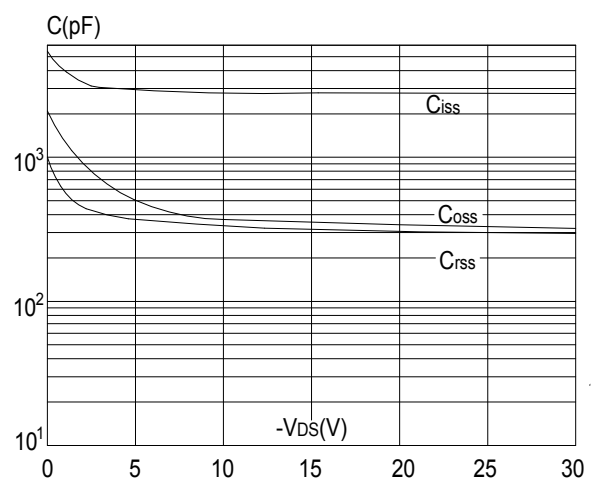
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

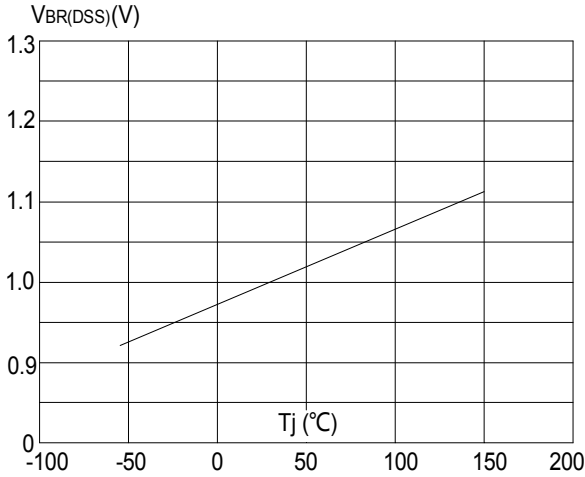


**Figure 6: Capacitance Characteristics**

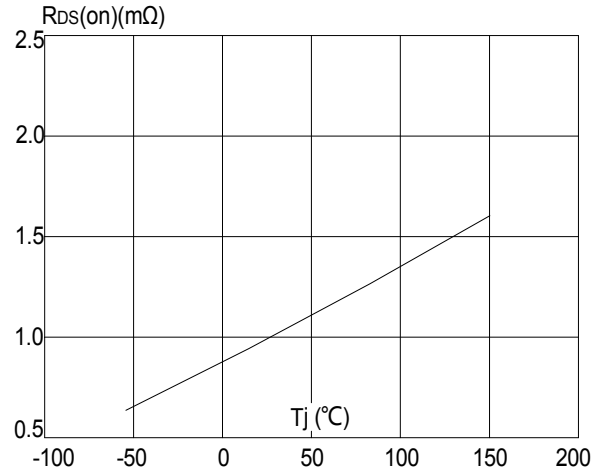




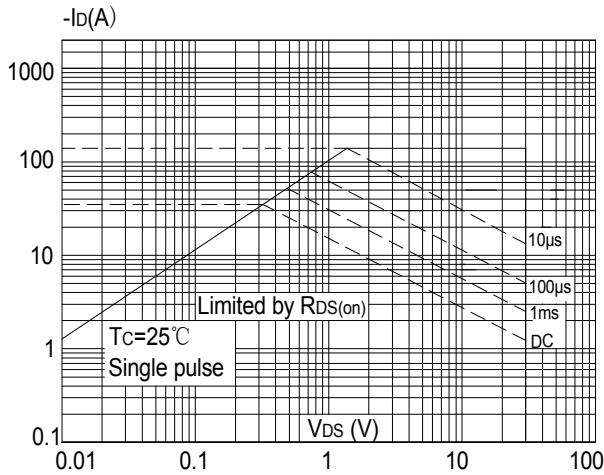
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



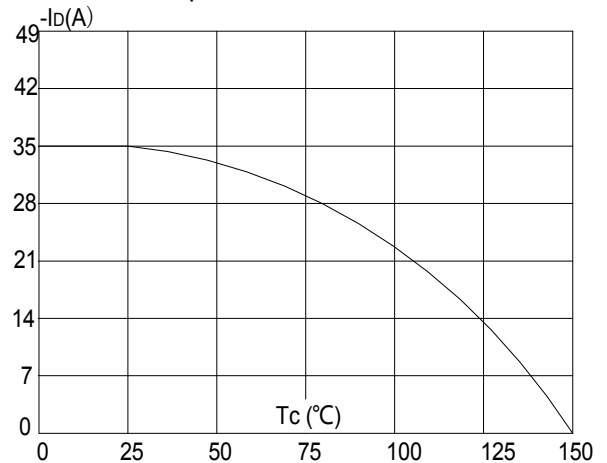
**Figure 8:** Normalized on Resistance vs. Junction Temperature



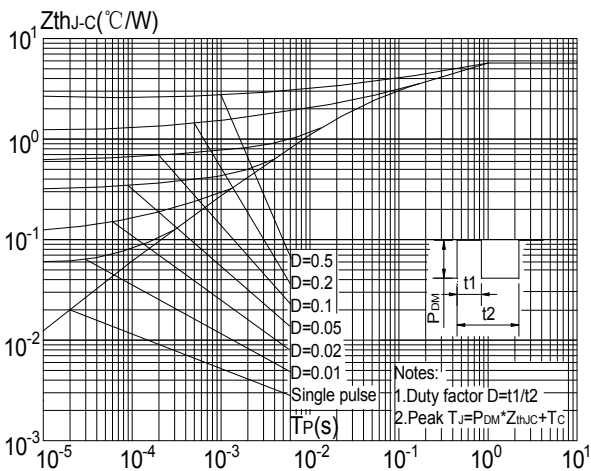
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case





### DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
$\theta$		10°	12°



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